Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 30 A



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PRIMARY CHARACTERISTICS							
I _{T(AV)}	20 A						
V _{DRM} /V _{RRM}	800 V, 1200 V						
V _{TM}	1.3 V						
I _{GT}	45 mA						
TJ	-40 °C to +125 °C						
Package	TO-247AC 3L						
Circuit configuration	Single SCR						

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding and battery charge

DESCRIPTION

The VS-30TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	20	^		
I _{RMS}		30	- A		
V _{RRM} /V _{DRM}		800 to 1200	V		
I _{TSM}		300	A		
V _T	20 A, T _J = 25 °C	1.3	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS										
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA							
VS-30TPS08-M3	800	900	10							
VS-30TPS12-M3	1200	1300	10							



VS-30TPS..-M3 Series



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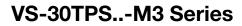
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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_{\rm C}$ = 95 °C, 180° conduction	half sine wave	20		
Maximum RMS on-state current	I _{RMS}			30	А	
Maximum peak, one-cycle		10 ms sine pulse, rated V_{RRN}	_A applied	250	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage	10 ms sine pulse, no voltage reapplied			
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM}	_A applied	310	A ² s	
Maximum - t for fusing	1-1	10 ms sine pulse, no voltage	442	A-5		
Maximum I²√t for fusing	l²√t	t = 0.1 to 10 ms, no voltage	4420	A²√s		
Maximum on-state voltage drop	V _{TM}	20 A, T _J = 25 °C	1.3	V		
On-state slope resistance	r _t	T 125 °C		12	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.0	V	
Maximum reverse and direct leakage	1/1	T _J = 25 °C	$V_{R} = rated V_{RRM}/V_{DRM}$	0.5		
current	I _{RM} /I _{DM}	T _J = 125 °C	VR = Tated VRRM/ VDRM	10	mA	
Maximum holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C			ША	
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , R_g -k = open			V/µs	
Maximum rate of rise of turned-on current	dl/dt			150	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T_J = -10 °C	60	0	
Maximum required DC gate current to trigger	I _{GT}	I_{GT} Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		mA	
		Anode supply = 6 V, resistive load, T_J = 125 °C	20		
		Anode supply = 6 V, resistive load, T_J = -10 °C	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	v	
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	v	
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V reteducture	0.25		
Maximum DC gate current not to trigger	I _{GD}	$T_J = 125 \text{ °C}, V_{DRM} = \text{rated value}$	2.0	mA	

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t _{gt}	$T_J = 25 \text{ °C}$	0.9						
Typical reverse recovery time	t _{rr}	T ₁ = 125 °C	4	μs					
Typical turn-off time	tq	1] = 125 C	110						

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	YMBOL TEST CONDITIONS		UNITS				
Maximum junction and storage temperature range		TJ, T _{Stg}		-40 to +125	°C				
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	0.8					
Maximum thermal resistance, junction to ambient		R _{thJA}			°C/W				
Maximum thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.2					
Approximate weight				6	g				
Approximate weight				0.21	oz.				
Mounting torque	minimum			6 (5)	kgf · cm				
Mounting torque	maximum			12 (10)	(lbf ⋅ in)				
				30TPS08					
warking device	Marking device		Case style TO-247AC 3L	30TPS12					

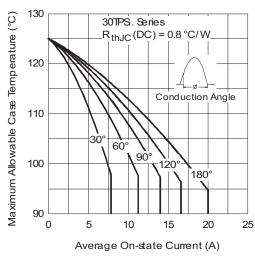
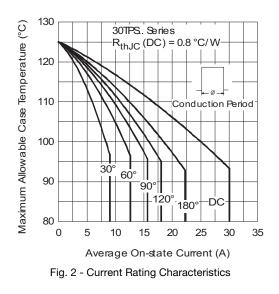


Fig. 1 - Current Rating Characteristics



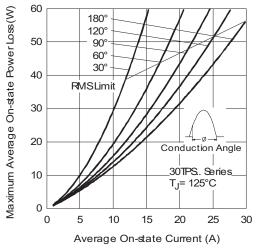
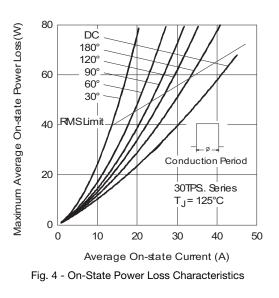


Fig. 3 - On-State Power Loss Characteristics



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3

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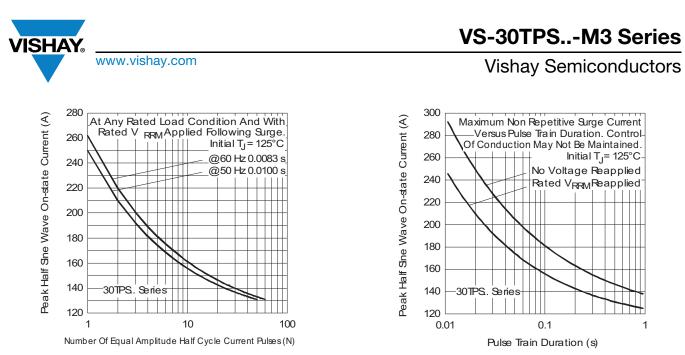
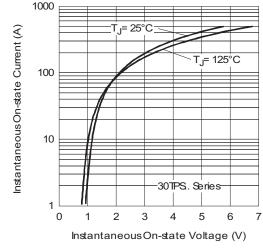
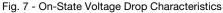
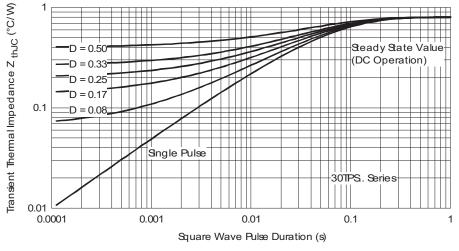




Fig. 6 - Maximum Non-Repetitive Surge Current





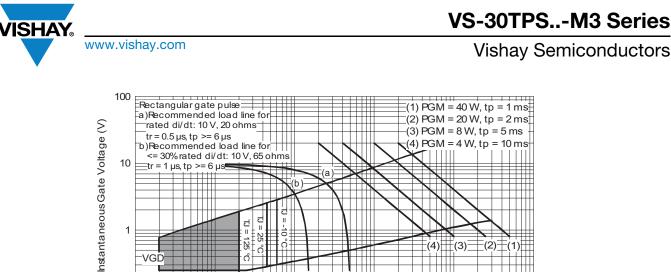




 Revision: 26-Feb-2019
 4
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ද් || ರ = 125 25 (2) (1) (4) (3) റ് റ്

Frequency Limited by PG(AV)

10

100

Instantaneous Gate Current (A)

1

Fig. 9 - Gate Characteristics

30TPS. Series

0.1

ORDERING INFORMATION TABLE

1

0.1 0.001

VGD

IGD

0.01

Device code	VS-	30	т	Р	s	12	-M3	
		2	3	4	5	6	7	
	1 - 2 - 3 -	Cur	rent rati	iiconduc ng (30 =	: 30 A)	oduct		
	4 -	T = Pac	thyristo kage: TO-247	r				
	5 -	Typ S =	e of silio standar		•			B = 800 V
	7 -	Envi	ronmen	tal digit:				= 1200 V terminations lead (Pb)-

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-30TPS08-M3	25	500	Antistatic plastic tubes						
VS-30TPS12-M3	25	500	Antistatic plastic tubes						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96138					
Part marking information	www.vishay.com/doc?95007					

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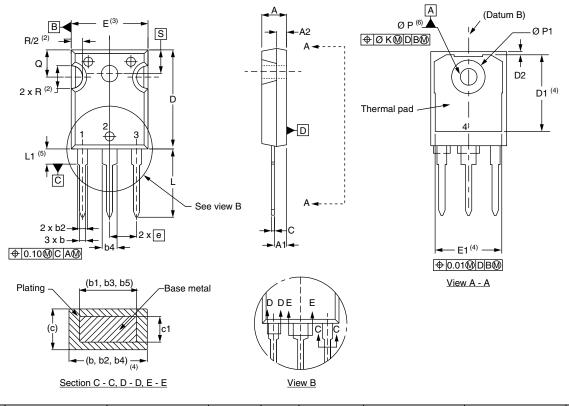
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TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	5 BSC	
b1	0.99	1.35	0.039	0.053			ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			ØΡ	3.56	3.66	0.14	0.144	
b5	2.59	3.38	0.102	0.133			Ø P1	-	7.39	-	0.291	
С	0.38	0.89	0.015	0.035			Q	5.31	5.69	0.209	0.224	
c1	0.38	0.84	0.015	0.033			R	4.52	5.49	0.178	0.216	
D	19.71	20.70	0.776	0.815	3		S	5.51	BSC	0.217	' BSC	
D1	13.08	-	0.515	-	4							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension Q

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1



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